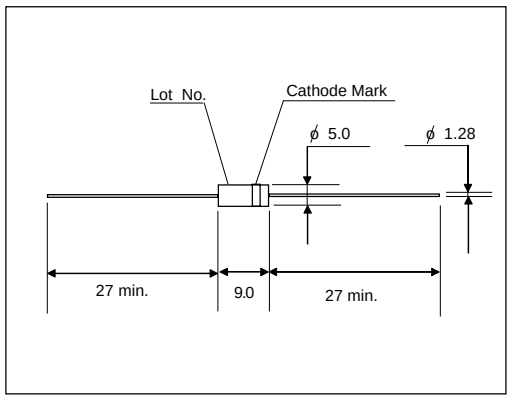
HVCA™

BR4F

4.0kV 0.8A HIGH VOLTAGE DIODES

BR4F is high reliability resin molded type high voltage diode in small size package which is sealed a multilayed mesa type silicon chip by epoxy resin.

■ Outline Drawings : mm



■ Features

- High speed switching
- High Current
- High surge resisitivity for CRT discharge
- High reliability design
- High Voltage

■ Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

■ Cathode Mark

Type	Mark
BR4F	

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items	Symbols	Condition	BR4F	Units
Repetitive Peak Renerse Voltage	V_{RRM}		4.0	kV
Average Output Current	I_O	Ta=25°C,Resistive Load	0.8	A peak
Suege Current	I_{FSM}		20	A peak
Junction Temperature	Tj		155	°C
Allowable Operation Case Temperature	Tc		125	°C
Storage Temperature	T_{stg}		-40 to +155	°C

● Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	BR4F	Units
Maximum Forward Voltage Drop	V_F	at 25°C,I_F =$I_{F(AV)}$	11	V
Maximum Reverse Current	IR1	at 25°C,V_R =V_{RRM}	5.0	uA
	IR2	at 100°C,V_R =V_{RRM}	50	uA
Maximum Reverse Recovery Time	Trr	at 25°C	150	nS
Junction Capacitance	Cj	at 25°C,V_R=0V,f=1MHz	--	pF

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